L Number	Hits	Search Text	DB	Time stamp
1	403	438/197.ccls. and substrate	USPAT	2003/10/31 10:01
2	233	438/197.ccls. and substrate and conductive	USPAT	2003/10/31
3	138	438/197.ccls. and substrate and conductive and dielectric	USPAT	2003/10/31
4	371	438/197.ccls. and substrate and conductive and dielectric ahnd "buried drain"	USPAT	2003/10/31 10:05
5	0	438/197.ccls. and substrate and conductive and dielectric and "buried"	USPAT	2003/10/31 10:05
6	127	drain" 438/197.ccls. and substrate and conductive and dielectric and drain	USPAT	2003/10/31
7	99	438/197.ccls. and substrate and crain conductive and dielectric and drain and insulat94	USPAT	2003/10/31
8	97	438/197.ccls. and substrate and conductive and dielectric and drain and insulat\$4 and silicon	USPAT	2003/10/31 10:05
9	21	438/197.ccls. and substrate and conductive and dielectric and drain and insulat\$4 and silicon and cap	USPAT	2003/10/31 10:06
10	19	438/197.ccls. and substrate and conductive and dielectric and drain and insulat\$4 and silicon and cap and pattern\$4	USPAT	2003/10/31 10:06
11	19	438/197.ccls. and substrate and conductive and dielectric and drain and insulat\$4 and silicon and cap and pattern\$4 and gate	USPAT	2003/10/31 10:06
12	8	438/197.ccls. and substrate and conductive and dielectric and drain and insulat\$4 and silicon and cap and	USPAT	2003/10/31 10:06
13	0	pattern\$4 and gate and word 438/197.ccls. and substrate and conductive and dielectric and drain and insulat\$4 and silicon and cap and	USPAT	2003/10/31 10:06
14	8	pattern\$4 and gate and word and liner 438/197.ccls. and substrate and conductive and dielectric and drain and insulat\$4 and silicon and cap and	USPAT	2003/10/31 10:07
16	1	pattern\$4 and gate and word and line\$4 438/197.ccls. and substrate and conductive and dielectric and drain and insulat\$4 and silicon and cap and pattern\$4 and gate and word and line\$4	USPAT	2003/10/31 10:19
17	0	and metal and salicide 438/197.ccls. and substrate and "strip stack"	USPAT	2003/10/31 10:19
18	0	438/197.ccls. and substrate and "strip stacked"	USPAT	2003/10/31
19	88	438/197.ccls. and substrate and stack	USPAT	2003/10/31
20	86	438/197.ccls. and substrate and stack and gate	USPAT	2003/10/31 10:20
21	57	438/197.ccls. and substrate and stack and gate and conductive	USPAT	2003/10/31 10:20
22	41	438/197.ccls. and substrate and stack and gate and conductive and dielectric	USPAT	2003/10/31 10:20
23	40	438/197.ccls. and substrate and stack and gate and conductive and dielectric and	USPAT	2003/10/31 10:20
24	4	drain 438/197.ccls. and substrate and stack and gate and conductive and dielectric and	USPAT	2003/10/31 10:20
25	4	drain and bit 438/197.ccls. and substrate and stack and gate and conductive and dielectric and	USPAT	2003/10/31 10:21
[i		drain and bit and insulat\$4		

26	4	438/197.ccls. and substrate and stack and gate and conductive and dielectric and	USPAT	2003/10/31 10:21
		drain and bit and insulat\$4 and silicon		
27	3	438/197.ccls. and substrate and stack and	USPAT	2003/10/31
		gate and conductive and dielectric and drain and bit and insulat\$4 and silicon		10:21
		and cap		
28	3	438/197.ccls. and substrate and stack and	USPAT	2003/10/31
		gate and conductive and dielectric and drain and bit and insulat\$4 and silicon		10:21
		and cap and pattern\$4		
29	3	438/197.ccls. and substrate and stack and	USPAT	2003/10/31
		gate and conductive and dielectric and drain and bit and insulat\$4 and silicon		10:21
		and cap and pattern\$4 and word		
30	3	438/197.ccls. and substrate and stack and	USPAT	2003/10/31
		gate and conductive and dielectric and drain and bit and insulat\$4 and silicon		10:21
		and cap and pattern\$4 and word and line		
31	0	438/197.ccls. and substrate and stack and	USPAT	2003/10/31
		gate and conductive and dielectric and		10:21
		drain and bit and insulat\$4 and silicon and cap and pattern\$4 and word and line		
		and liner		
32	3	438/197.ccls. and substrate and stack and	USPAT	2003/10/31
		gate and conductive and dielectric and drain and bit and insulat\$4 and silicon		10.22
		and cap and pattern\$4 and word and line		
33	0	and metal 438/197.ccls. and substrate and stack and	USPAT	2003/10/31
33	0	gate and conductive and dielectric and	USPAI	10:22
		drain and bit and insulat\$4 and silicon		
		and cap and pattern\$4 and word and line		
34	3	and metal and salicide 438/197.ccls. and substrate and stack and	USPAT	2003/10/31
"		gate and conductive and dielectric and		10:22
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15	8	438/197.ccls. and substrate and	USPAT	2003/10/31
		conductive and dielectric and drain and insulat\$4 and silicon and cap and		11:08
		pattern\$4 and gate and word and line\$4		
		and metal		0000/10/01
-	387	438/197.ccls.	USPAT	2003/10/31 10:00
_	378	438/197.ccls. and substrate	USPAT	2003/07/16
				11:58
-	89	438/197.ccls. and substrate and "conductive layer"	USPAT	2003/07/16 11:51
_	39	438/197.ccls. and substrate and	USPAT	2003/07/16
		"conductive layer" and "dielectric layer"		11:51
-	0	438/197.ccls. and substrate and "conductive layer" and "dielectric layer"	USPAT	2003/07/16 11:51
		and "buried drain"		
-	37	438/197.ccls. and substrate and	USPAT	2003/07/16
		"conductive layer" and "dielectric layer" and "drain"		11:52
-	10	438/197.ccls. and substrate and	USPAT	2003/07/16
		"conductive layer" and "dielectric layer"		11:52
_	3	and "drain" and "insulating layer" 438/197.ccls. and substrate and	USPAT	2003/07/16
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_	0	438/197.ccls. and substrate and	USPAT	2003/07/16
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